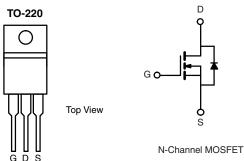


Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.009			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.013			
I _D (A)	50			
Configuration	Single			



FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified^d
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



COMPLIANT HALOGEN

ORDERING INFORMATION	
Package	TO-220
Lead (Pb)-free and Halogen-free	SQP50N06-09L-GE3

ABSOLUTE MAXIMUM RATINGS (To	_c = 25 °C, unles	s otherwise noted	(k		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	60	N/	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C ^a	I-	50		
Continuous Drain Current	T _C = 125 °C	I _D	49		
Continuous Source Current (Diode Conduction) ^a		I _S	50	А	
Pulsed Drain Current ^b		I _{DM}	200		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	48		
Single Pulse Avalanche Energy		E _{AS}	115	mJ	
Maximum Dawar Dissinctionh	T _C = 25 °C	PD	136	W	
Maximum Power Dissipation ^b	T _C = 125 °C	۲D	45	vv	
Operating Junction and Storage Temperature Ran	ge	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	50	°C/W
Junction-to-Case (Drain)		R _{thJC}	1.1	0/10

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 $\mu s,\,duty\,cycle \leq$ 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static						1	-	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} =	= 0 V, I _D = 250 μΑ	60	-	-		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA	
-		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.0071	0.0090		
Durin Country On Otata Desistances		$V_{GS} = 10 V$	I _D = 20 A, T _J = 125 °C	-	-	0.0160		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0190	Ω	
		$V_{GS} = 4.5 V$	I _D = 10 A	-	0.0094	0.0130		
Forward Transconductanceb	9 _{fs}	V _{DS}	= 15 V, I _D = 20 A	-	62	-	S	
Dynamic ^b	-			-				
Input Capacitance	C _{iss}			-	2451	3065		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	435	545	pF	
Reverse Transfer Capacitance	C _{rss}			-	192	240		
Total Gate Charge ^c	Qg			-	48	72		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 50 \text{ A}$	-	7.1	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	13.5	-		
Gate Resistance	R _g	f = 1 MHz		0.85	1.7	2.6	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	10	15		
Rise Time ^c	t _r	$\label{eq:V_DD} \begin{array}{l} V_{\text{DD}} = 30 \text{ V}, \ R_{\text{L}} = 0.6 \ \Omega \\ I_{\text{D}} \cong 50 \text{ A}, \ V_{\text{GEN}} = 10 \text{ V}, \ R_{g} = 1 \ \Omega \end{array}$		-	11	17	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	27	41		
Fall Time ^c	t _f			-	8	12		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	200	A	
Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		-	0.82	1.5	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

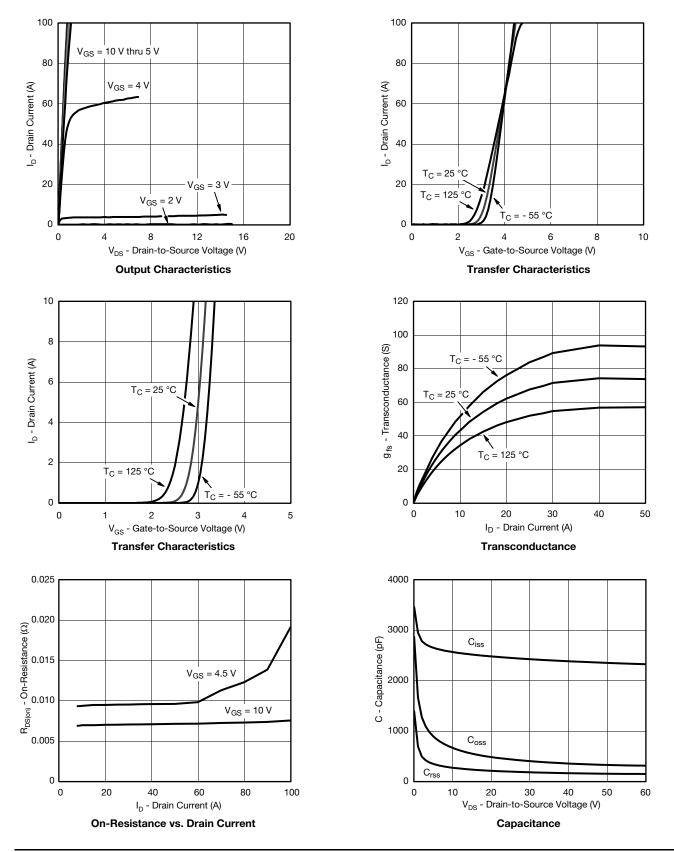
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



S12-1867-Rev. A, 13-Aug-12

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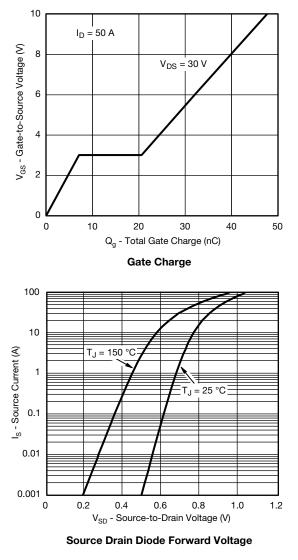
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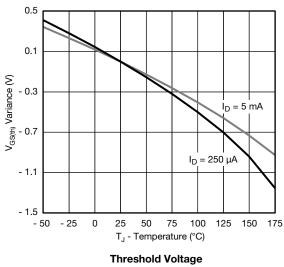
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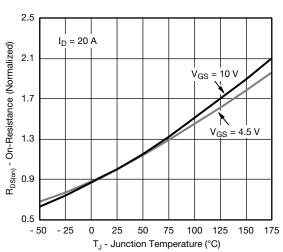


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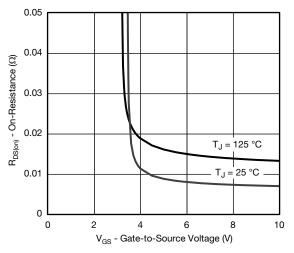
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



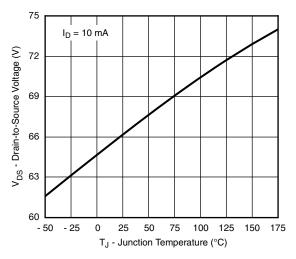




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



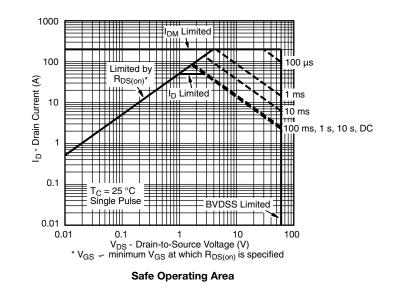
Drain Source Breakdown vs. Junction Temperature

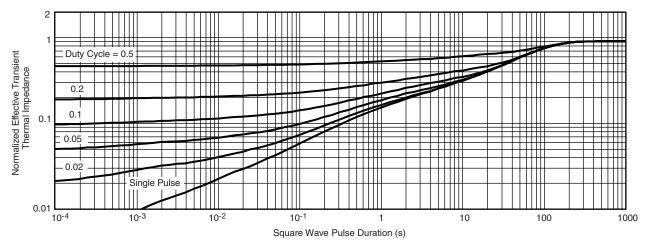
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



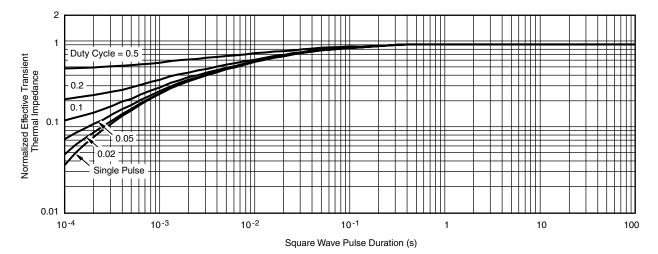


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

· The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62664.



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TO-220AB



	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
А	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
С	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
е	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
ØР	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
	0413-Rev. P,		0.102	0.118

Note

 * M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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